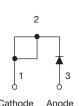


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**Vishay Semiconductors** 

# Fast Soft Recovery Rectifier Diode, 20 A





**TO-220 FULL-PAK** 

Cathode	Anoc

PRODUCT SUMMARY				
Package	TO-220FP			
I <sub>F(AV)</sub>	20 A			
V <sub>R</sub>	200 V, 400 V, 600 V			
V <sub>F</sub> at I <sub>F</sub>	1.3 V			
I <sub>FSM</sub>	300 A			
t <sub>rr</sub>	60 ns			
T <sub>J</sub> max.	150 °C			
Diode variation	Single die			
Snap factor	0.6			

### **FEATURES**

- · Glass passivated pellet chip junction
- 150 °C max. operation junction temperature • Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 approved
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **APPLICATIONS**

These devices are intended for use in output rectification and freewheeling in inverters, choppers and converters as well as in input rectification where severe restrictions on conducted EMI should be met.

#### DESCRIPTION

The VS-20ETF0..FP... fast soft recovery rectifier series has been optimized for combined short reverse recovery time and low forward voltage drop.

The glass passivation ensures stable reliable operation in the most severe temperature and power cycling conditions.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL CHARACTERISTICS VALUES UNI							
I <sub>F(AV)</sub>	Sinusoidal waveform	20	А				
V <sub>RRM</sub>		200 to 600	V				
I <sub>FSM</sub>		300	А				
V <sub>F</sub>	10 A, T <sub>J</sub> = 25 °C	1.2	V				
t <sub>rr</sub>	1 A, 100 A/µs	60	ns				
TJ		-40 to +150	°C				

VOLTAGE RATINGS							
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> AT 150 °C mA				
VS-20ETF02FPPbF, VS-20ETF02FP-M3	200	300					
VS-20ETF04FPPbF, VS-20ETF04FP-M3	400	500	5				
VS-20ETF06FPPbF, VS-20ETF06FP-M3	600	700					

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum average forward current	I <sub>F(AV)</sub>	$T_C = 51$ °C, 180° conduction half sine wave	20				
Maximum peak one cycle non-repetitive	I <sub>FSM</sub>	10 ms sine pulse, rated $V_{\text{RRM}}$ applied	250	А			
surge current		10 ms sine pulse, no voltage reapplied	300				
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	316	A <sup>2</sup> s			
Maximum From fusing		10 ms sine pulse, no voltage reapplied	442	A-5			
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	4420	A²√s			

RoHS COMPLIANT HALOGEN FREE





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ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS	
Maximum forward voltage drop	V	20 A, T <sub>J</sub> = 25 °C	20 A, T <sub>J</sub> = 25 °C		V	
Maximum forward voltage drop	V <sub>FM</sub>	60 A, T <sub>J</sub> = 25 °C		1.67		
Forward slope resistance	r <sub>t</sub>	T <sub>J</sub> = 150 °C		12.5	mΩ	
Threshold voltage	V <sub>F(TO)</sub>	T <sub>J</sub> = 150 °C		0.9	V	
		T <sub>J</sub> = 25 °C	$V_{B} = Rated V_{BBM}$	0.1	mA	
Maximum reverse leakage current	I <sub>RM</sub>	T <sub>J</sub> = 150 °C	VR - naieu VRRM	5.0		

RECOVERY CHARACTERISTICS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	<b>↑</b>		
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> at 20 A <sub>pk</sub>	160	ns			
Reverse recovery current	Irr	100 A/µs	10	A	$t_a \mid t_b$		
Reverse recovery charge	Q <sub>rr</sub>	25 °C	1.25	μC	dir/ dt		
Snap factor	S	Typical	0.6				

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and temperature range	storage	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C	
Maximum thermal resist junction to case	stance,	R <sub>thJC</sub>	DC operation	2.5		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.5		
Approvimate weight				2	g	
Approximate weight				0.07	oz.	
Mounting torgue	minimum			6 (5)	kgf · cm	
Mounting torque	maximum			12 (10)	(lbf · in)	
Marking device				20ETF	02FP	
			Case style TO-220 FULL-PAK	20ETF04FP		
				20ETF	06FP	



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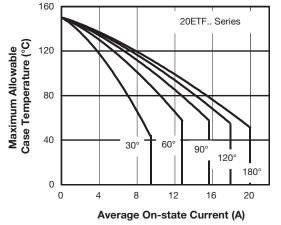


Fig. 1 - Current Rating Characteristics

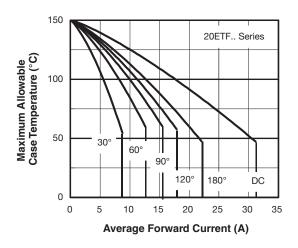
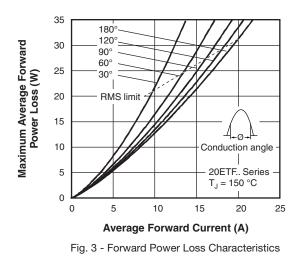


Fig. 2 - Current Rating Characteristics



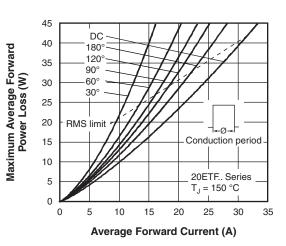
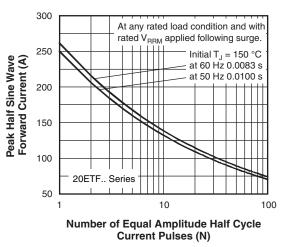


Fig. 4 - Forward Power Loss Characteristics





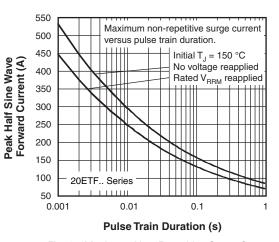


Fig. 6 - Maximum Non-Repetitive Surge Current

Revision: 11-Feb-16

3

Document Number: 94095

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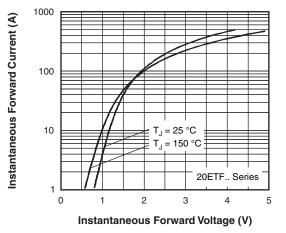


Fig. 7 - Forward Voltage Drop Characteristics

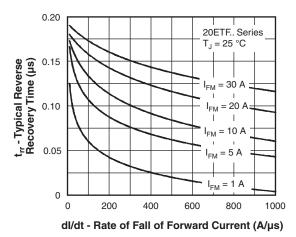


Fig. 8 - Recovery Time Characteristics,  $T_J = 25 \degree C$ 

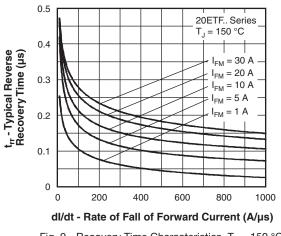


Fig. 9 - Recovery Time Characteristics, T<sub>J</sub> = 150 °C

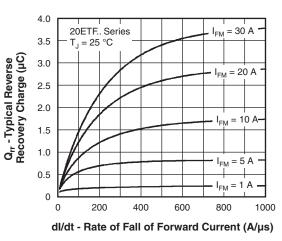


Fig. 10 - Recovery Charge Characteristics, T<sub>J</sub> = 25 °C

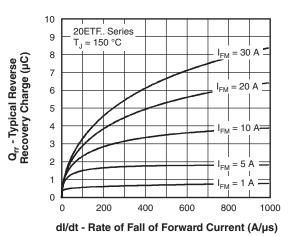


Fig. 11 - Recovery Charge Characteristics,  $T_J = 150 \text{ }^{\circ}\text{C}$ 

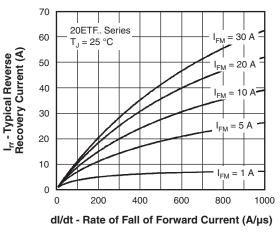


Fig. 12 - Recovery Current Characteristics,  $T_{\rm J}$  = 25  $^\circ C$ 

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4

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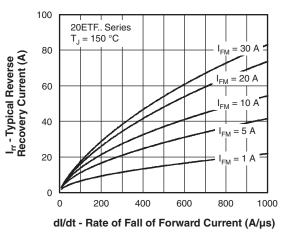
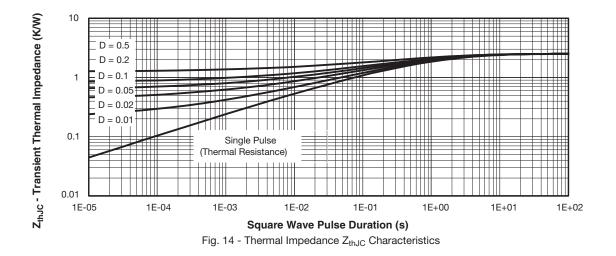


Fig. 13 - Recovery Current Characteristics, T<sub>J</sub> = 150 °C





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#### **ORDERING INFORMATION TABLE**

Device code	VS-	20	E	т	F	06	FP	PbF
		2	3	4	5	6	7	8
	<ol> <li>Vishay Semiconductors product</li> <li>Current rating (20 = 20 A)</li> <li>Circuit configuration: E = single diode</li> <li>Package: T = TO-220</li> <li>Type of silicon:</li> </ol>							
	6 - 7 - 8 -	Vol FUI Env	tage coo _L-PAK ⁄ironmer bF = lea	t recove de x 100 ntal digit d (Pb)-fi	= V <sub>RRN</sub> : ree and	RoHS-0	- 04 = 4 06 = 0	200 V 400 V 600 V

• -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-20ETF02FPPbF	50	1000	Antistatic plastic tubes				
VS-20ETF02FP-M3	50	1000	Antistatic plastic tubes				
VS-20ETF04FPPbF	50	1000	Antistatic plastic tubes				
VS-20ETF04FP-M3	50	1000	Antistatic plastic tubes				
VS-20ETF06FPPbF	50	1000	Antistatic plastic tubes				
VS-20ETF06FP-M3	50	1000	Antistatic plastic tubes				

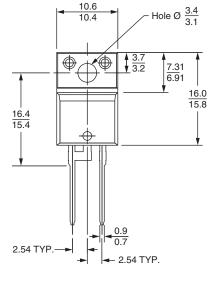
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95005					
Deut erendeinen information	TO-220 FP PbF	www.vishay.com/doc?95009			
Part marking information	TO-220 FP -M3	www.vishay.com/doc?95440			
SPICE model		www.vishay.com/doc?95410			



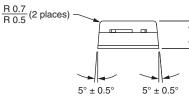
# **Outline Dimensions**

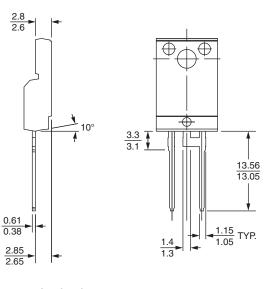
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## **DIMENSIONS** in millimeters



 $\frac{4.8}{4.6}$ 





Lead assignments Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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